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(54) **SEMICONDUCTOR DEVICE INCLUDING CAPACITOR STRUCTURE AND METHOD FOR MANUFACTURING THE SAME**

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(57) **ABSTRACT**

A semiconductor device of the disclosure includes a substrate, a capacitor contact structure electrically connected to the substrate, a lower electrode connected to the capacitor contact structure, a capacitor insulating layer covering the lower electrode, and an upper electrode covering the capacitor insulating layer. The upper electrode includes a multiple layer on the capacitor insulating layer, and a cover layer on the multiple layer. The multiple layer includes a first electrode layer, a second electrode layer, and a first metal silicide layer between the first and second electrode layers. A work function of the first metal silicide layer is greater than a work function of the first electrode layer and a work function of the second electrode layer.

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